

UTM2054

Preliminary

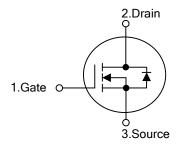
N-CHANNEL ENHANCEMENT MODE

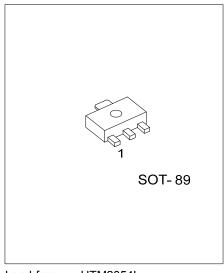
DESCRIPTION

The **UTM2054** uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with low gate voltages. This device is suitable for use as a load switch or in PWM applications.

FEATURES

- * $R_{DS(ON)}$ = 35m Ω @V_{GS}=10V
- * $R_{DS(ON)}$ = 45m Ω @V_{GS}=4.5V
- * $R_{DS(ON)}$ = 110m Ω @V_{GS}=2.5V
- * Ultra low gate charge (typical 11.5 nC)
- * Low reverse transfer capacitance (C_{RSS} = typical 60 pF)
- * Fast switching capability
- * Avalanche energy specified
- * Improved dv/dt capability, high ruggedness
- SYMBOL





Lead-free: UTM2054L Halogen-free: UTM2054G

ORDERING INFORMATION

Ordering Number			Dookogo	Pin Assignment			Dealing
Normal	Lead Free	Halogen Free	Package	1	2	3	Packing
UTM2054-AB3-R	UTM2054L-AB3-R	UTM2054G-AB3-R	SOT-89	G	D	S	Tape Reel

UTM2054L <u>-AB</u> 3-R	(1) R: Tape Reel
(2)Package Type	(2) AB3: SOT-89
(3)Lead Plating	(3) G: Halogen Free, L: Lead Free, Blank: Pb/Sn

ABSOLUTE MAXIMUM RATINGS (T_a =25°C, unless otherwise specified)

			r	1	
PARAMETER		SYMBOL	RATINGS	UNIT	
Drain-Source Voltage		V _{DSS}	20	V	
Gate-Source Voltage		V _{GSS}	±16	V	
	Continuous	I _D	5	A	
Drain Current (V _{GS} =10V)	Pulsed	I _{DM}	20		
Diode Continuous Forward Current		Is	3	А	
Power Dissipation		PD	1.47	W	
Junction Temperature		TJ	150	°C	
Storage Temperature		T _{STG}	-55 ~ +150	°C	

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ ELECTRICAL CHARACTERISTICS (T_a=25°C, unless otherwise specified)

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PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250µA	20			V	
Drain-Source Leakage Current	I _{DSS}	V _{DS} =16V, V _{GS} =0V			1	μA	
Gate-Source Leakage Current	I _{GSS}	V_{DS} =0V, V_{GS} =±16V			±100	nA	
ON CHARACTERISTICS							
Gate Threshold Voltage	V _{GS(TH)}	$V_{DS}=V_{GS}$, $I_{D}=250\mu A$	0.6	0.9	1.5	V	
Statia Drain Source On State Desistance	R _{DS(ON)}	V _{GS} =10V, I _{DS} =5A		35	40		
Static Drain-Source On-State Resistance		V _{GS} =4.5V, I _{DS} =3.5A		45	54	mΩ	
(Note)		V _{GS} =2.5V, I _{DS} =2.5A		110	130		
DYNAMIC CHARACTERISTICS							
Input Capacitance	CISS			450		pF	
Output Capacitance	C _{OSS}	V _{DS} =15V, V _{GS} =0V, f=1.0MHz		100		pF	
Reverse Transfer Capacitance	C _{RSS}			60		pF	
Gate resistance	R _G	V _{GS} =0V, V _{DS} =0V, f=1MHz		2.5		Ω	
SWITCHING CHARACTERISTICS							
Turn-On Delay Time	t _{D(ON)}			7	10	ns	
Turn-On Rise Time	t _R	V _{DD} =10V, R _L =10Ω, I _{DS} =1A,		15	25	ns	
Turn-Off Delay Time	t _{D(OFF)}	V_{GEN} =4.5V, R_{G} =6 Ω		19	26	ns	
Turn-Off Fall Time	t _F	7		6	7	ns	
Total Gate Charge	Q _G			11.5	15	nC	
Gate-Source Charge	Q _{GS}	V _{DS} =10V, V _{GS} =4.5V, I _{DS} =5 A		3.8		nC	
Gate-Drain Charge	Q _{DD}	7		5.2		nC	
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Diode Forward Voltage (Note)	V _{SD}	I _{SD} =3A, V _{GS} =0V		0.7	1.3	V	
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Note: Pulse width \leq 300µs, Duty cycle \leq 2%

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